Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

IN THE CLAIMS

- 1. (original) A system, comprising:
 - a controller; and
 - a memory device coupled to the controller to receive signals therefrom, and comprising:

an array of memory cells arranged in a plurality of addressable banks, each bank comprises addressable rows and columns of memory cells;

a mode register; and

address circuitry coupled to the mode register to configure the addressable banks in response to a program state of the mode register.

- (original) The system of claim 1 wherein the addressable banks can be configured as 2. either four or eight banks.
- (original) The system of claim 1 wherein the address circuitry selectively routes address 3. signal to either a row decoder or a bank decoder in response to the mode register.
- 4. (original) A system, comprising:
 - a controller; and
 - a dynamic random access memory device coupled to the controller and comprising:

an array of X memory cells;

a mode register; and

address circuitry coupled to the mode register to configure the array in response to a program state of the mode register, wherein the mode register defines a number of addressable banks of the array.

- (original) The system of claim 4 wherein a first state of the mode register configures the 5. array into Y banks each having X/Y memory cells, and a second state of the mode register configures the array into Z banks each having X/Z memory cells.
- 6. (original) The system of claim 4 wherein the address circuitry comprises column, row and bank address decoders.

Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

- 7. (original) The system of claim 6 wherein the address circuitry routes a selected address input signal to either the row or bank decoder in response to the mode register.
- 8. (original) The system of claim 7 wherein the address circuitry comprises a multiplex circuit.
- 9. (original) A system, comprising:
 - a controller; and
- a synchronous dynamic random access memory (SDRAM) coupled to the controller and comprising:

an array of X memory cells;

- a mode register;
- a column address decoder;
- a row address decoder;
- a bank address decoder; and

address signal circuitry coupled to a plurality of address signal input connections, the address signal circuitry routes a selected one of the plurality of address input connections to either the row or bank address decoder in response to data stored in the mode register.

- 10. (original) The system of claim 9 wherein a first state of the mode register configures the array into Y banks each having X/Y memory cells, and a second state of the mode register configures the array into Z banks each having X/Z memory cells.
- 11. (original) The system of claim 10 wherein X = 4 and Z = 8.
- 12. (original) A system, comprising:

a controller; and

a synchronous dynamic random access memory (SDRAM) coupled to the controller and comprising:

an array of X memory cells;

at least one external input connection to receive a configuration signal;

logic circuitry coupled to the at least one external input connection;

- a column address decoder;
- a row address decoder;

a bank address decoder; and

address signal circuitry coupled to a plurality of address signal input connections, the address signal circuitry routes a selected one of the plurality of address input connections to either the row or bank address decoder in response to the logic circuitry.

- 13. (original) The system of claim 12 wherein a first state of the logic circuitry configures the array into Y banks each having X/Y memory cells, and a second state of the logic circuitry configures the array into Z banks each having X/Z memory cells.
- 14. (original) The system of claim 13 wherein X = 4 and Z = 8.
- 15. (original) The system of claim 12 wherein the at least one external input connection comprises two input connections to receive a two-bit configuration signal.
- 16. (original) A system, comprising:

a controller; and

a memory device coupled to the controller to receive signals including an input signal therefrom, and comprising:

an array of memory cells arranged in a plurality of addressable banks, each bank comprises addressable rows and columns of memory cells;

a decode circuit to decode the input signal; and

address circuitry coupled to the decode circuit to configure the addressable banks in response to a program state of the input signal.

- 17. (original) The system of claim 16 wherein the addressable banks can be configured as either four or eight banks.
- 18. (original) The system of claim 16 wherein the address circuitry selectively routes address signal to either a row decoder or a bank decoder in response to the input signal.
- 19. (original) The system of claim 16, wherein the input signal is a one-bit binary input.

Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

- 20. (original) The system of claim 16, wherein the input signal is a multi-bit binary input and the number of banks is configurable.
- 21. (original) The system of claim 20, wherein the number of banks is four or eight.
- 22. (original) A system, comprising:
 - a controller providing an input signal; and
 - a dynamic random access memory device coupled to the controller and comprising:

an array of X memory cells;

a decode circuit to decode the input signal; and

address circuitry coupled to the decode circuit to configure the array in response to a program state of the input signal, wherein the input signal defines a number of addressable banks of the array.

- 23. (original) The system of claim 21 wherein a first state of the input signal configures the array into Y banks each having X/Y memory cells, and a second state of the input signal configures the array into Z banks each having X/Z memory cells.
- 24. (original) The system of claim 22 wherein the address circuitry comprises column, row and bank address decoders.
- 25. (original) The system of claim 24 wherein the address circuitry routes a selected address input signal to either the row or bank decoder in response to the controller input signal.
- 26. (original) The system of claim 22 wherein the address circuitry comprises a multiplex circuit.
- 27. (original) A memory device, comprising:

an array of memory cells arranged in a plurality of addressable banks, each bank comprises addressable rows and columns of memory cells;

a decode circuit to decode an external input signal; and

address circuitry coupled to the decode circuit to configure the addressable banks in response to a program state of the external input signal.

Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

28. (original) The memory device of claim 27 wherein the addressable banks can be configured as either four or eight banks.

- 29. (original) The memory device of claim 27 wherein the address circuitry selectively routes address signal to either a row decoder or a bank decoder in response to the external input signal.
- 30. (previously presented) A dynamic random access memory comprising:
 an array of X memory cells;
 a decode circuit to decode an external input signal; and
 address circuitry coupled to the decode circuit to configure the array in response to a
 program state of the external input signal, wherein the input signal defines a number of
 addressable banks of the array.
- 31. (previously presented) The dynamic random access memory of claim 30 wherein a first state of the input signal configures the array into Y banks each having X/Y memory cells, and a second state of the mode register configures the array into Z banks each having X/Z memory cells.
- 32. (original) The dynamic random access memory of claim 30 wherein the address circuitry comprises column, row and bank address decoders.
- 33. (original) The dynamic random access memory of claim 32 wherein the address circuitry routes a selected address input signal to either the row or bank decoder in response to the external input signal.
- 34. (original) The dynamic random access memory of claim 33 wherein the address circuitry comprises a multiplex circuit.
- 35. (original) A synchronous dynamic random access memory (SDRAM) comprising:an array of X memory cells;a decode circuit to decode an external input signal;

Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

- a column address decoder;
- a row address decoder;
- a bank address decoder; and

address signal circuitry coupled to a plurality of address signal input connections, the address signal circuitry routes a selected one of the plurality of address input connections to either the row or bank address decoder in response to data decoded by the decode circuit.

- 36. (original) The SDRAM of claim 35 wherein a first state of the external input signal configures the array into Y banks each having X/Y memory cells, and a second state of the external input signal configures the array into Z banks each having X/Z memory cells.
- 37. (original) The SDRAM of claim 36 wherein X = 4 and Z = 8.
- 38. (original) A method of operating a memory device comprising:
 receiving an external input signal at decode circuitry of the memory device; and
 adjusting address circuitry of the memory device in response to the decoded external
 input signal, wherein the address circuitry configures a number of addressable banks of a
 memory cell array.
- 39. (original) The method of claim 38 wherein the address circuitry routes an externally provided address signal to either a bank address decoder or a row address decoder.
- 40. (original) The method of claim 38 wherein the memory device comprises X rows, Y columns and Z banks, where the array comprises X*Y*Z memory cells.
- 41. (original) The method of claim 40 where the Z banks are configurable to 2, 4, 8 or 16 banks.
- 42. (original) A method of operating a memory system comprising:
 outputting decode circuitry data from a processor to a memory device, wherein the
 decode circuitry decodes an external input signal to generate bank count data; and

Serial No. 10/781,125

Title: USER SELECTABLE BANKS FOR DRAM

adjusting address circuitry of the memory device in response to the decoded external input signal, wherein the address circuitry configures a number of addressable banks of a memory cell array using the bank count data.

- 43. (original) The method of claim 42 wherein the external input signal data comprises one bit of data.
- 44. (original) The method of claim 42 wherein the address circuitry routes externally address signals provided by the processor to either a bank address decoder or a row address decoder of the memory device.